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Kind regards,

Team Nexperia

# PSMN004-36B

## N-channel TrenchMOS SiliconMAX logic level FET

Rev. 02 — 1 March 2010

Product data sheet

## 1. Product profile

### 1.1 General description

SiliconMAX logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

### 1.3 Applications

- DC-to-DC convertors
- Switched-mode power supplies

### 1.4 Quick reference data

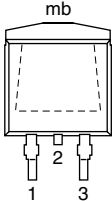
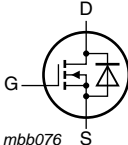
Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	36	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 5\text{ V};$ see <a href="#">Figure 1</a> and <a href="#">3</a>	-	-	75	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	-	230	W
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 5\text{ V}; I_D = 75\text{ A}; V_{DS} = 15\text{ V};$ $T_j = 25\text{ °C};$ see <a href="#">Figure 11</a>	-	39	-	nC
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$ see <a href="#">Figure 9</a> and <a href="#">10</a>	-	3.5	4	m $\Omega$
		$V_{GS} = 5\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$ see <a href="#">Figure 9</a> and <a href="#">10</a>	-	4	5	m $\Omega$



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p style="text-align: center;">SOT404 (D2PAK)</p>	 <p style="text-align: center;"><i>mbb076</i></p>
2	D	drain <a href="#">[1]</a>		
3	S	source		
mb	D	mounting base; connected to drain		

[1] It is not possible to make connection to pin 2.

## 3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PSMN004-36B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

### 4. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

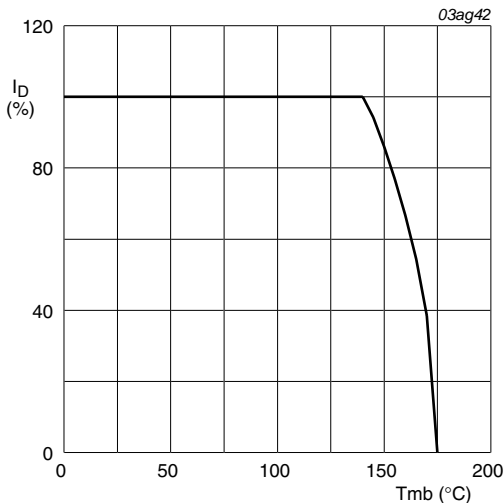
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	36	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	36	V
V <sub>GS</sub>	gate-source voltage		-15	15	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 100 °C; see <a href="#">Figure 1</a>	-	75	A
		V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 1</a> and <a href="#">3</a>	-	75	A
I <sub>DM</sub>	peak drain current	t <sub>p</sub> ≤ 10 μs; pulsed; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 3</a>	-	240	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <a href="#">Figure 2</a>	-	230	W
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
V <sub>GSM</sub>	peak gate-source voltage	pulsed; δ = 25 %; t <sub>p</sub> ≤ 50 μs; T <sub>j</sub> ≤ 150 °C	-20	20	V

Source-drain diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	75	A
I <sub>SM</sub>	peak source current	t <sub>p</sub> ≤ 10 μs; pulsed; T <sub>mb</sub> = 25 °C	-	240	A

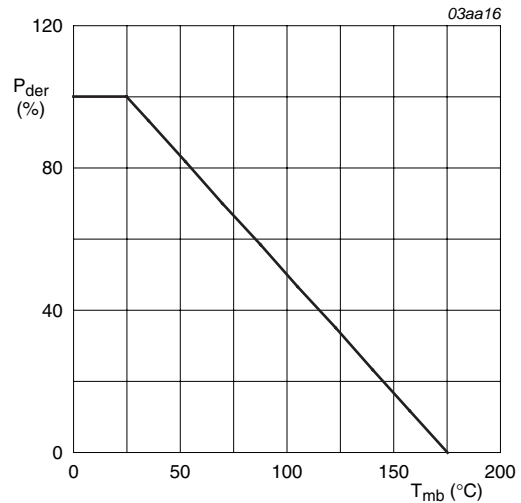
  

Avalanche ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	V <sub>GS</sub> = 5 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 75 A; V <sub>sup</sub> = 15 V; unclamped; t <sub>p</sub> = 0.1 ms; R <sub>GS</sub> = 50 Ω	-	120	mJ
I <sub>AS</sub>	non-repetitive avalanche current	V <sub>sup</sub> = 15 V; V <sub>GS</sub> = 5 V; T <sub>j(init)</sub> = 25 °C; R <sub>GS</sub> = 50 Ω; unclamped	-	75	A



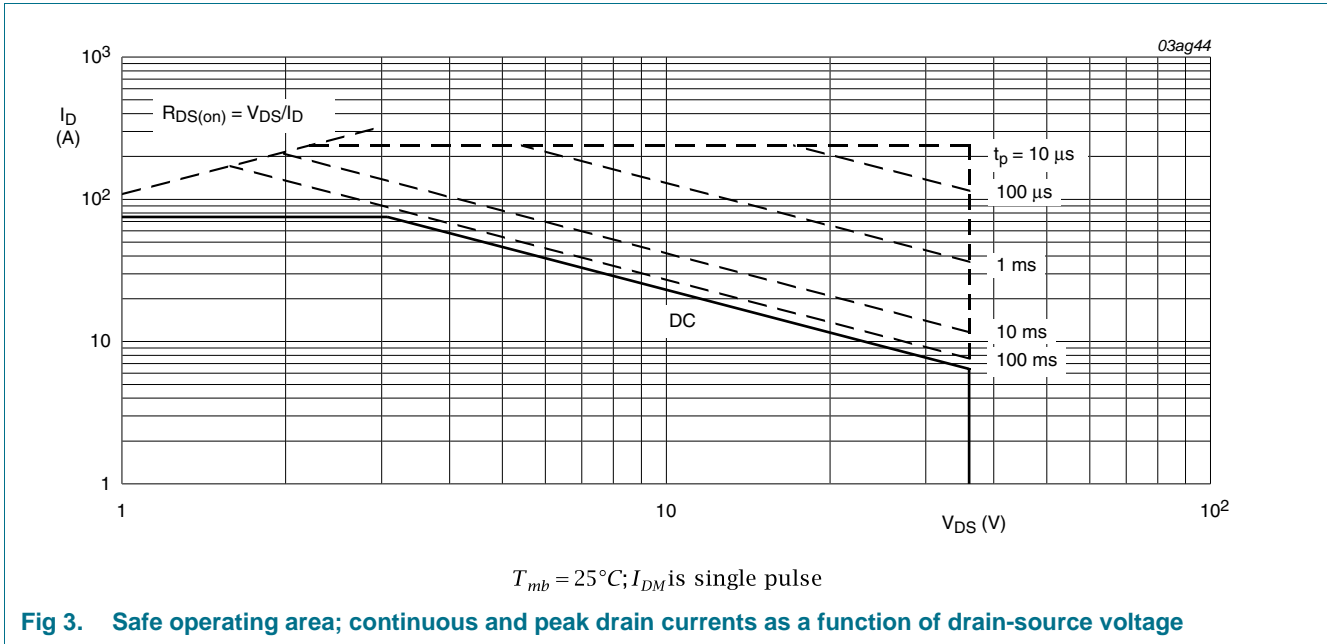
$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100\%$$

**Fig 1. Normalized continuous drain current as a function of mounting base temperature**



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

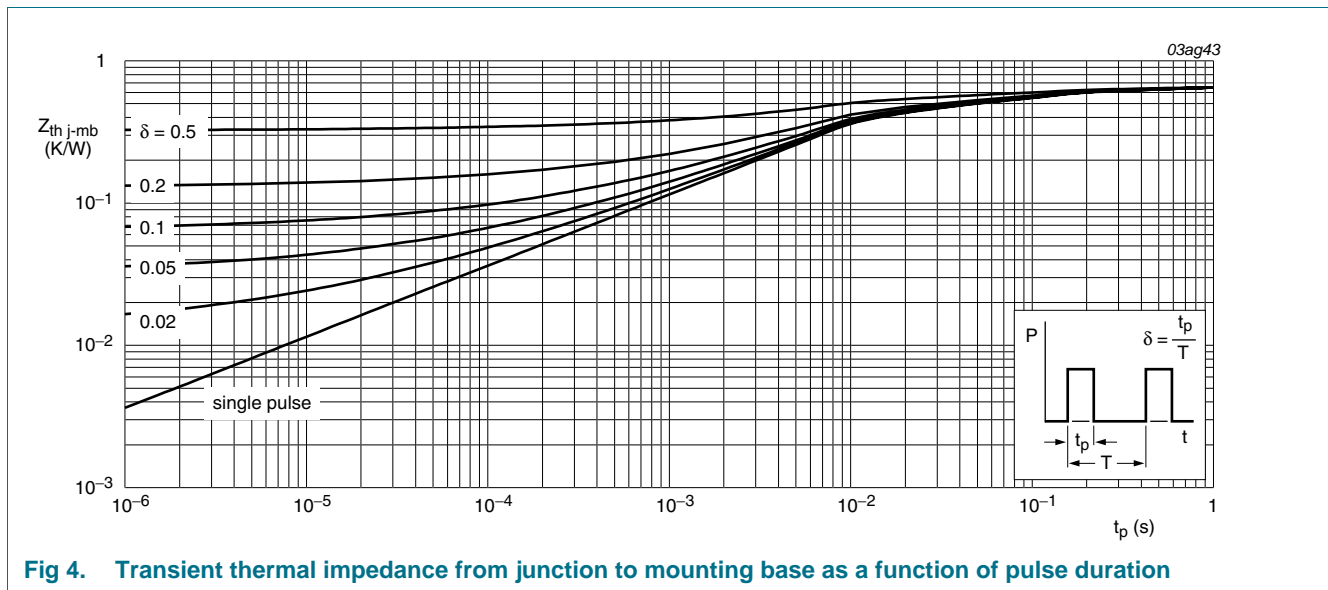
**Fig 2. Normalized total power dissipation as a function of mounting base temperature**



### 5. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	-	0.65	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	-	50	K/W

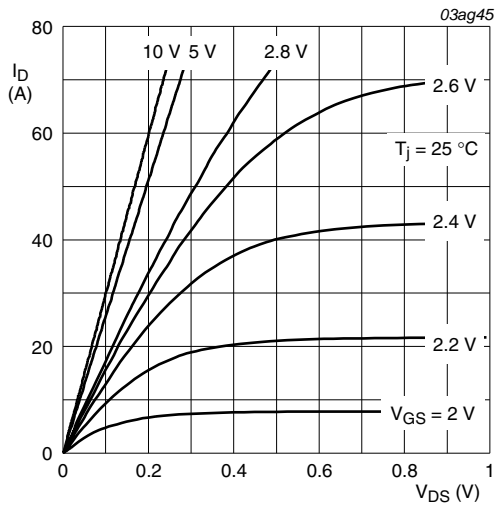


**Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration**

## 6. Characteristics

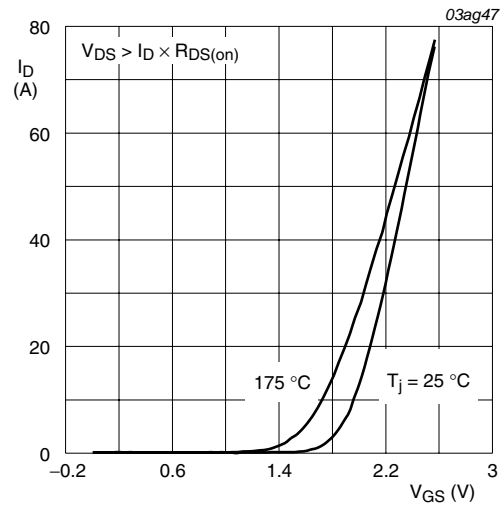
**Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	36	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	32	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 8</a>	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 8</a>	-	-	2.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 8</a>	1	1.5	2	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.05	10	$\mu\text{A}$
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	1	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	1	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 9</a> and <a href="#">10</a>	-	3.5	4	m $\Omega$
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 9</a> and <a href="#">10</a>	-	-	9.25	m $\Omega$
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 9</a> and <a href="#">10</a>	-	-	5.4	m $\Omega$
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 9</a> and <a href="#">10</a>	-	4	5	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 75 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 5 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 11</a>	-	97	-	nC
$Q_{GS}$	gate-source charge		-	20	-	nC
$Q_{GD}$	gate-drain charge		-	39	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 12</a>	-	6000	-	pF
$C_{oss}$	output capacitance		-	1700	-	pF
$C_{rss}$	reverse transfer capacitance		-	1400	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 1.2 \text{ } \Omega; V_{GS} = 5 \text{ V}; R_{G(ext)} = 6 \text{ } \Omega; T_j = 25 \text{ }^\circ\text{C}$	-	45	-	ns
$t_r$	rise time		-	220	-	ns
$t_{d(off)}$	turn-off delay time		-	435	-	ns
$t_f$	fall time		-	320	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 75 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 13</a>	-	1.1	-	V
		$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 13</a>	-	0.85	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20 \text{ A}; di_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V}$ ;	-	400	-	ns
$Q_r$	recovered charge	$V_{DS} = 25 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	1	-	$\mu\text{C}$



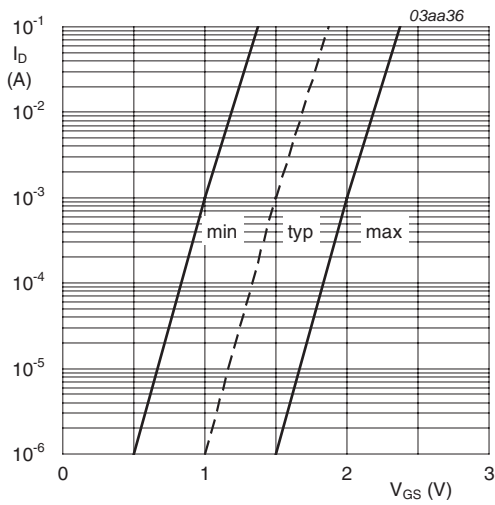
$T_j = 25^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



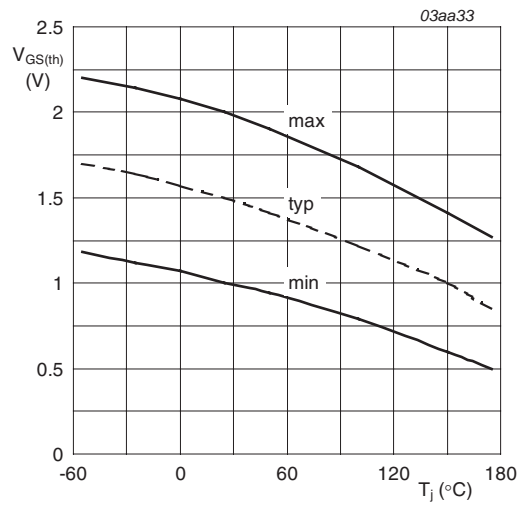
$T_j = 25^\circ\text{C}$  and  $175^\circ\text{C}; V_{DS} > I_D \times R_{DS(on)}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$T_j = 25^\circ\text{C}; V_{DS} = V_{GS}$

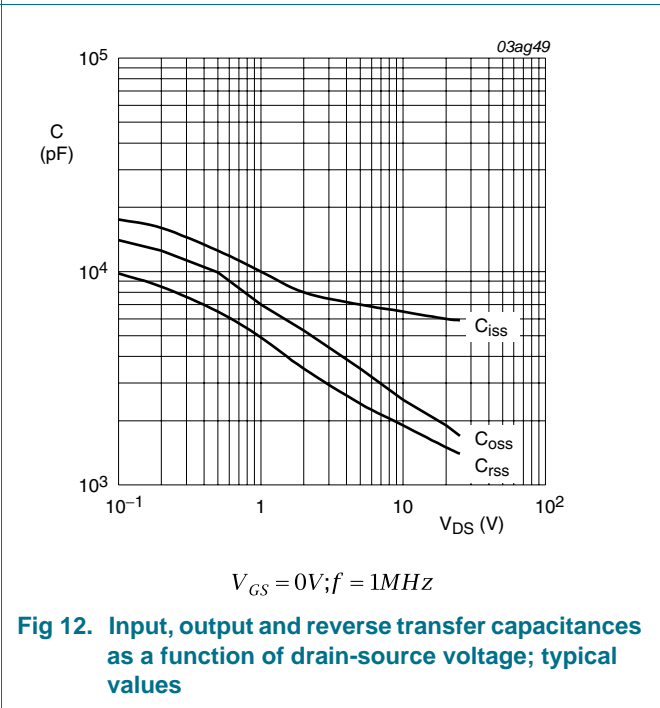
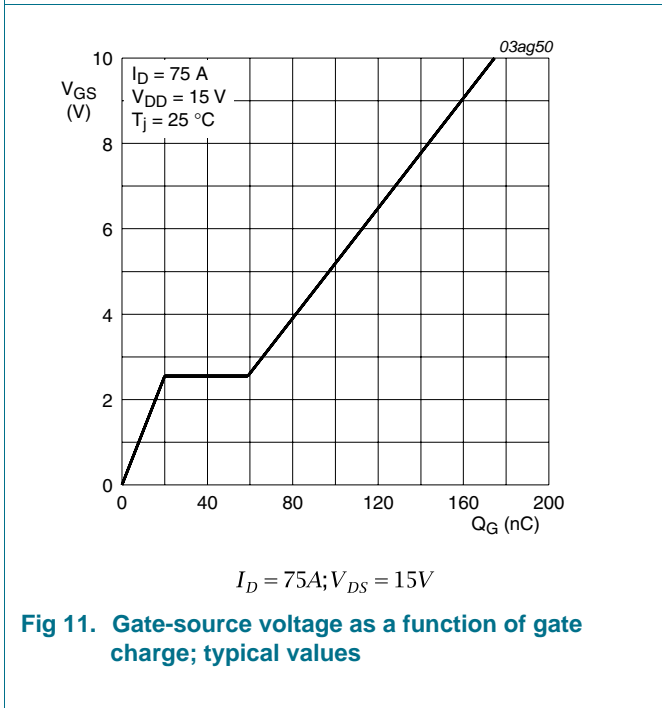
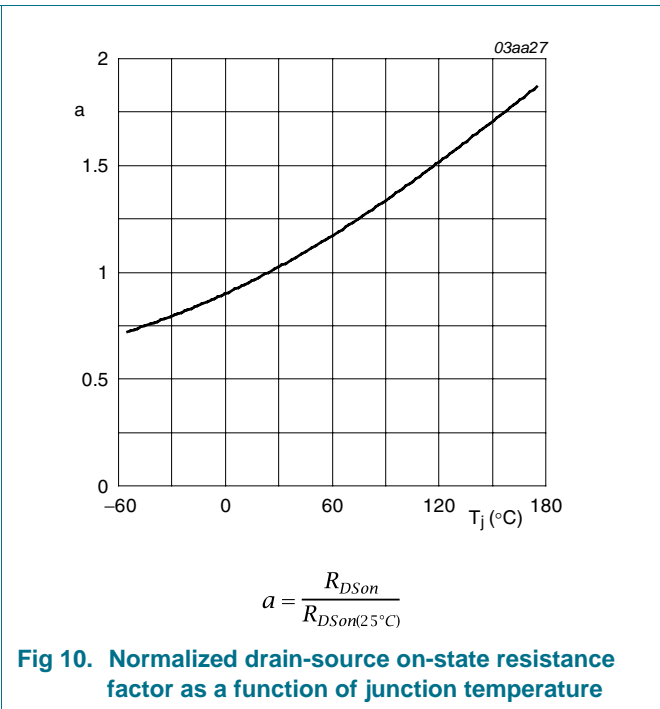
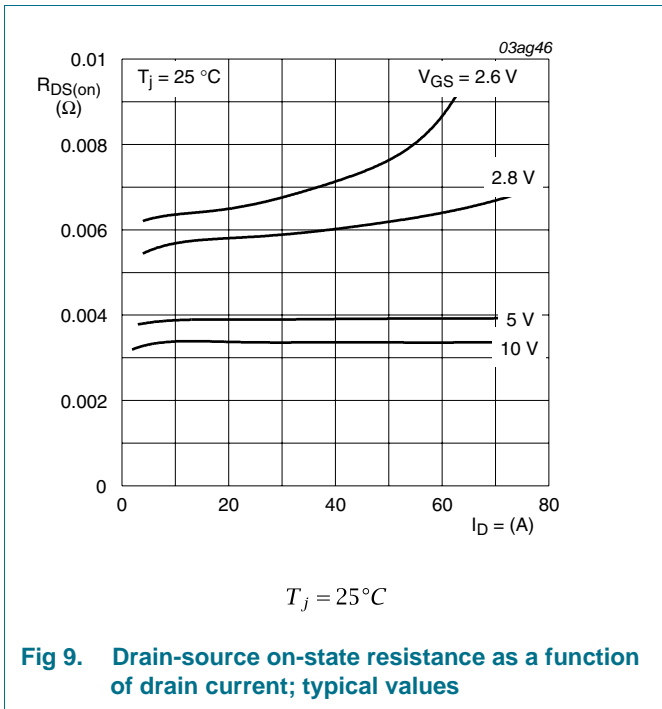
Fig 7. Sub-threshold drain current as a function of gate-source voltage

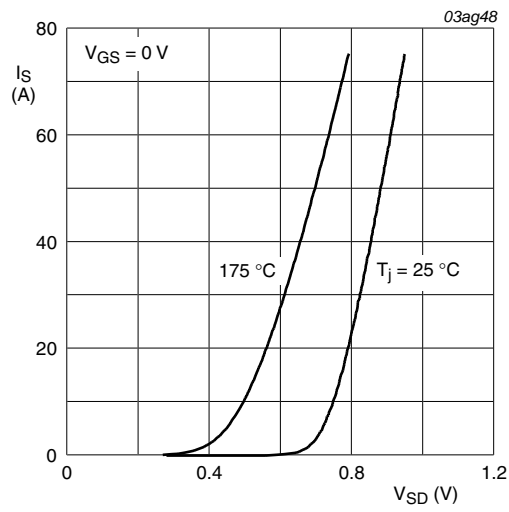


$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

Fig 8. Gate-source threshold voltage as a function of junction temperature







$T_j = 25^\circ\text{C}$  and  $175^\circ\text{C}; V_{GS} = 0\text{V}$

Fig 13. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404

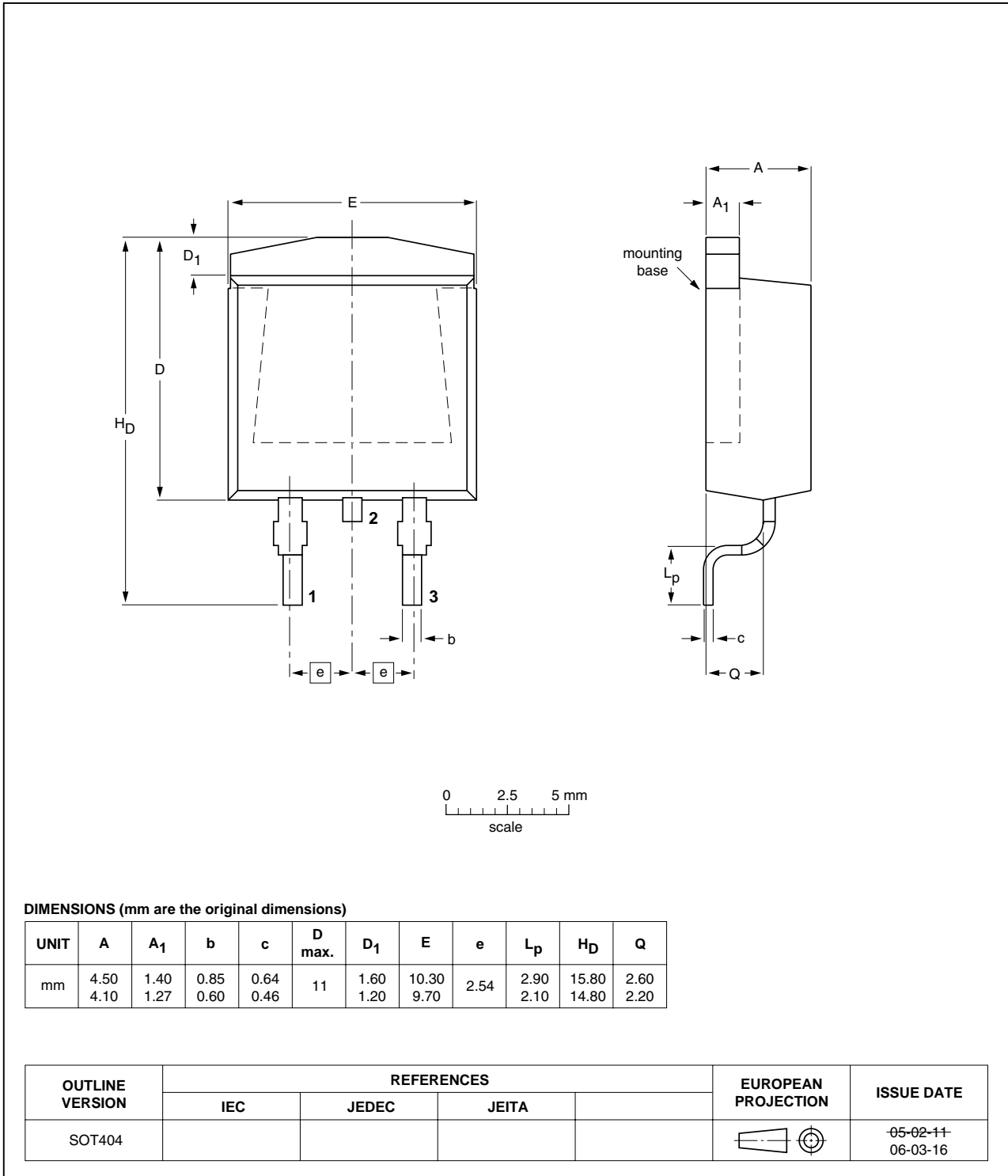


Fig 14. Package outline SOT404 (D2PAK)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN004-36B_2	20100301	Product data sheet	-	PSMN004_36P_36B-01
Modifications:				
				<ul style="list-style-type: none"><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li><li>• Type number PSMN004-36B_2 separated from data sheet PSMN004_36P_36B-01.</li></ul>
PSMN004_36P_36B-01	20011119	Product data	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Date of release: 1 March 2010

Document identifier: PSMN004-36B\_2